

High-reliability discrete products and engineering services since 1977

# 3N204-3N205

## DUAL GATE MOSFET VHF AMPLIFIER

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Characteristic		Symbol	Min	Тур	Max	Unit
SMALL SIGNAL CHARACTERISTICS						
Forward transfer admittance <sup>(3)</sup>						
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, V_{G1S} = 0, f = 1.0kHz)$	3N201, 3N202	Y <sub>fs</sub>	8.0	12.8	20	mmhos
	3N203		7.0	12.5	15	
Input capacitance						5
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_D = I_{DSS}, f = 1.0MHz)$		C <sub>iss</sub>	-	3.3	-	pF
Reverse transfer capacitance		6				
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_D = 10mAdc, f = 1.0MHz)$		C <sub>rss</sub>	0.005	0.014	0.03	pF
Output capacitance		_				ρF
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_D = I_{DSS}, f = 1.0MHz)$	C <sub>oss</sub>	-	1.7	-	μг	
FUNCTIONAL CHARACTERISTICS						
Noise figure						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	NF	-	1.8	4.5	dB
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		-	5.3	6.0	
Common source power gain						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	$G_{ps}$	15	20	25	dB
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		20	25	30	
$(V_{DD} = 18Vdc, f_{LO} = 245MHz, f_{RF} = 200MHz)$	3N202	G <sub>c</sub> (5)	15	19	25	
Bandwidth						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	B <sub>w</sub>	5.0	-	9.0	MHz
$(V_{DD} = 18Vdc, f_{LO} = 245MHz, f_{RF} = 200MHz)$	3N202		4.5	-	7.5	
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		3.0	-	6.0	
Gain control gate-supply voltage (4)						
$(V_{DD} = 18Vdc, \Delta G_{ps} = -30dB, f = 200MHz)$	3N201	$V_{GG(GC)}$	0	-1.0	-3.0	Vdc
$(V_{DD} = 18Vdc, \Delta G_{ps} = -30dB, f = 45MHz)$	3N203		0	-0.6	-3.0	

### **ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C)**

CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage	V <sub>(BR)DSX</sub>	25	_	Vdc
$(I_D=10\mu A, V_{G1}=V_{G2}=-5.0V)$	▼ (BR)DSX	25	_	Vuc
Gate 1-Source Breakdown Voltage	V	+/-6	+/-30	Vdc
(I <sub>G1</sub> =+/- 10 mA) <sub>Note 1</sub>	$V_{(BR)G1SO}$	+/-0	+/-50	Vuc
Gate 2-Source Breakdown Voltage	V	+/-6	+/-30	Vdc
(I <sub>G2</sub> =+/-10mA) <sub>Note 1</sub>	$V_{(BR)G2SO}$	+/-0	+/-50	Vuc
Gate 1 Leakage Current	I <sub>G1SS</sub>	_	+/-10	nA
$(V_{G1S}=+/-5.0V, V_{G2S}=V_{DS}=0)$		-	+/-10	IIA
Gate 2 Leakage Current			+/-10	nA
$(V_{G2S}=+/-5.0V, V_{G1S}=V_{DS}=0)$	I <sub>G2SS</sub>	=	+/-10	na na
Gate 1 to Source Cutoff Voltage		-0.5	-4.0	Vdc
$(V_{DS}=15V, V_{G2S}=4.0V, I_{D}=20\mu A)$	V <sub>G1S(off)</sub>			



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### **ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C)**

CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT
Gate 2 to Source Cutoff Voltage $(V_{DS}{=}15V,V_{G1S}{=}0V,I_{D}{=}20\mu A)$	V <sub>G2S(off)</sub>	-0.2	-4.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current * (V <sub>DS</sub> =15V, V <sub>G2S</sub> =4.0V, V <sub>G1S</sub> =0V)	I <sub>DSS</sub> *	6	30	mA
SMALL SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V <sub>DS</sub> =15V, V <sub>G2S</sub> =4.0V, V <sub>G1S</sub> =0V, f=1.0kHz) <sub>Note 2</sub>	Y <sub>fs</sub>	10	22	mmhos
Input Capacitance $(V_{DS}=15V, V_{G2S}=4.0V, I_D=I_{DSS}, f=1.0Mhz)$	C <sub>iss</sub>	TYP.3.0		pF
Reverse Transfer Capacitance (V <sub>DS</sub> =15V, V <sub>GZS</sub> =4.0V, I <sub>D</sub> =10mA, f=1.0MHz)	C <sub>rss</sub>	0.005	0.03	pF
Output Capacitance $(V_{DS}=15V, V_{G2S}=4.0V, I_D=I_{DSS}, f=1.0MHz)$	C <sub>oss</sub>	TYP. 1.4		pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V <sub>DD</sub> =18V, V <sub>GG</sub> =7.0V, f=200MHz) 3N204 (V <sub>DS</sub> =15V, V <sub>GS</sub> =4.0V, I <sub>D</sub> =10mA, f=450MHZ) 3N204	NF		3.5 5.0	dB
Common Source Power Gain (V <sub>DD</sub> =18V, V <sub>GG</sub> =7.0V, f=200MHz) 3N204 (V <sub>DS</sub> =15V, V <sub>G2S</sub> =4.0V, I <sub>D</sub> =10mA, f=450MHz) 3N204	G <sub>ps</sub>	20 14	28	dB
$\label{eq:bandwidth} \begin{array}{ll} \textbf{Bandwidth} \\ (V_{DD}\!=\!18V, V_{GG}\!=\!7.0V, f\!=\!200\text{MHz}) & 3N204 \\ (V_{DD}\!=\!18V, f_{LO}\!=\!245\text{MHz}, f_{RF}\!=\!200\text{MHz})_{Note\ 4} & 3N205 \end{array}$	BW	7.0 4.0	12 7.0	MHz
Gain Control Gate Supply Voltage <sub>(Note 3)</sub> (V <sub>DD</sub> =18V, △GPS=300dB,f=200MHz) 3N204	$V_{\rm GG(GC)}$	0	-2.0	Vdc
Conversion Gain (Note 4) (V <sub>DD</sub> =18V, f <sub>LO</sub> =245MHz, f <sub>RF</sub> =200MHz) 3N205	G <sub>(conv.)</sub>	17	28	dB

<sup>\*</sup>PW=30 $\mu$ s, Duty Cycle  $\leq$  2.0%.

<sup>1)</sup> All gate breakdown voltages are measured while the device is conducting rated gate current. This insures that the gate voltage limiting network is functioning properly.

<sup>2)</sup> This parameter must be measured with bias voltages applied for less than five (5) seconds to avoid overheating.

<sup>3)</sup>  $\triangle G_{ps}$  is defined as the change in  $G_{ps}$  from the value at  $V_{GG}\text{=}7.0V.$ 

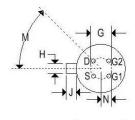
<sup>4)</sup> Amplitude at input from local oscillator is 3 volts RMS.

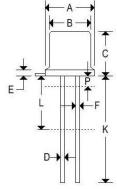


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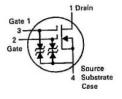
### **MECHANICAL CHARACTERISTICS**

Case:	TO-72
Marking:	Body painted, alpha-numeric
Pin out:	See below





	TO-72				
	Inches		Millim	eters	
	Min	Max	Min	Max	
Α	15	0.230		5.840	
В	12	0.195	74)	4.950	
С	H.	0.210	-	5.330	
D	(4)	0.021	360	0.530	
E		0.030	-	0.760	
F	(E)	0.019	250	0.480	
G	0.100	BSC	2.540 BSC		
Н	-	0.046	-	1.170	
J	320	0.048	(4)	1.220	
K	0.500	- 5	12.700	-	
L	0.250	- 1	(-)	6.350	
M	45° BSC		45° BSC		
N	0.050 BDC		1.270 BSC		
Р	(2)	0.050	74).	1.270	



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